Not Recommended for New Design Use DMG4406LSS





N-CHANNEL ENHANCEMENT MODE MOSFET

DMG8880LSS

Features

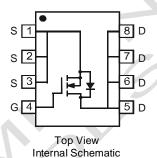
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
 - Weight: 0.072 grams (approximate)



Top View



Ordering Information (Note 4)

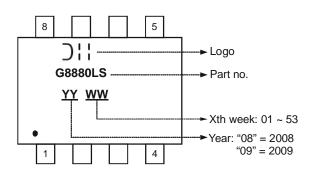
Part Number	Case	Packaging
DMG8880LSS-13	SO-8	2500 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information







$\label{eq:maximum Ratings} \textbf{@} T_{A} = 25^{\circ} \text{C unless otherwise specified}$

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5)	Steady State	$T_A = 25$ °C $T_A = 70$ °C	I _D	11.6 8.5	А
Pulsed Drain Current (Note 6)			I _{DM}	80	А

Thermal Characteristics

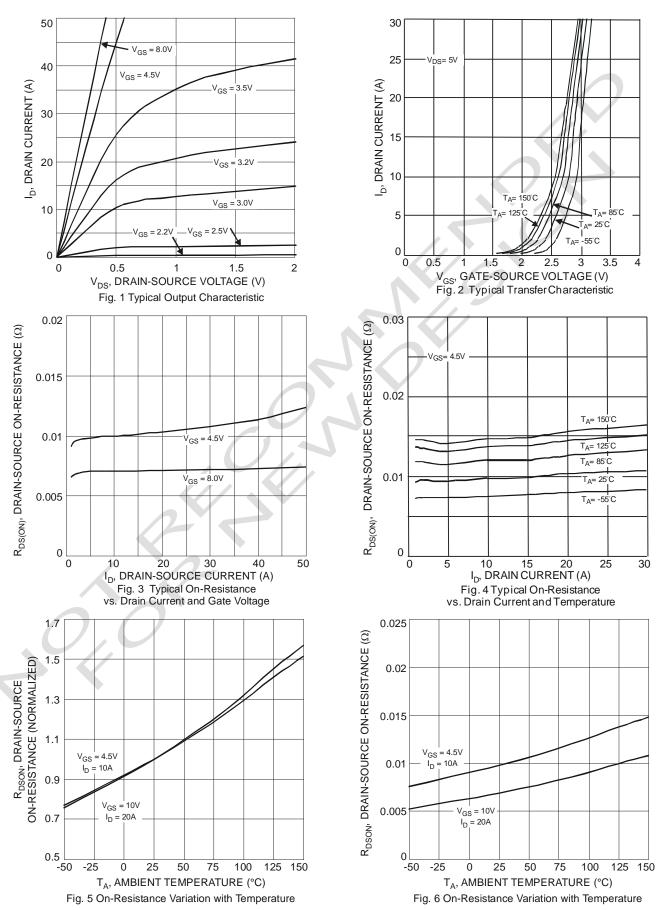
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	1.43	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 5)	R•JA	87	°C/W
Operating and Storage Temperature Range	T_J , T_{STG}	-55 to +150	°C

Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						•	
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	1.0	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	//.					•	
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.5	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	D		7.0 9.6	10 14	m•	V _{GS} = 10V, I _D = 11.6A	
Static Drain-Source On-Resistance	R _{DS (ON)}	-				$V_{GS} = 4.5V, I_D = 10.7A$	
Diode Forward Voltage	V_{SD}	-	0.7	1.0	V	$V_{GS} = 0V, I_S = 2.1A$	
DYNAMIC CHARACTERISTICS (Note 8)						•	
Input Capacitance	C _{iss}	-	1289	-	pF		
Output Capacitance	Coss	-	187	-	pF	$V_{DS} = 15V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	162	-	pF	11 = 1.0WHZ	
Gate Resistance	Rg	-	0.97	-	•	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge at 10V	Qg	ı	27.6	-	nC	$V_{GS} = 10V, V_{DS} = 15V,$ $I_D = 11.6A, I_G = 1.0mA$	
Total Gate Charge at 5V	Q_g	•	14.4	-	nC)/ 5)/)/ 45)/	
Gate-Source Charge	Q_{gs}	-	3.6	-	nC	$V_{GS} = 5V, V_{DS} = 15V,$ $I_{D} = 11.6A, I_{G} = 1.0mA$	
Gate-Drain Charge	Q_{gd}	-	4.9	-	nC		
Turn-On Delay Time	t _{D(on)}		7.04	-	ns		
Turn-On Rise Time	t _r	•	17.52	-	ns	V _{DD} = 15V, V _{GS} = 10V, R _{GS} = 11•, I _D = 11.6A	
Turn-Off Delay Time	t _{D(off)}	-	36.13	-	ns		
Turn-Off Fall Time	t _f	1	19.67	-	ns		

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- Repetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.







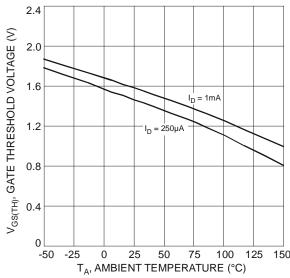
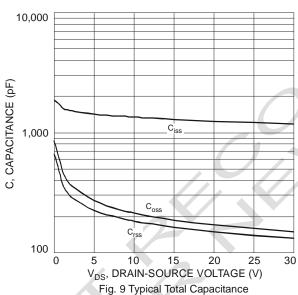
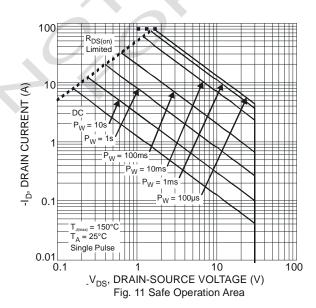
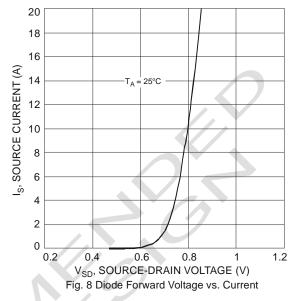
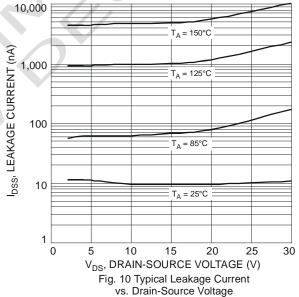


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

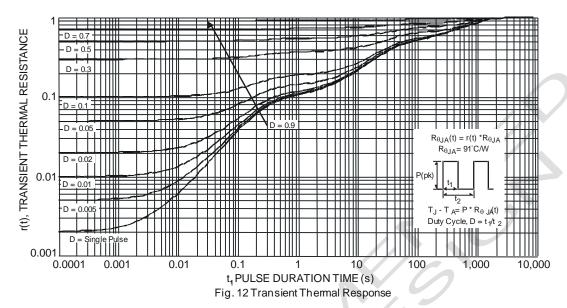




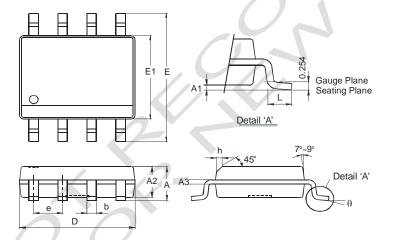






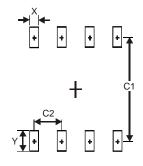


Package Outline Dimensions



SO-8					
Dim	Min	Max			
Α	•	1.75			
A1	0.10	0.20			
A2	1.30	1.50			
А3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	€ 1.27 Typ				
h	ı	0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Υ	1.55
C1	5.4
C2	1.27

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